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SEMICONDUCTOR

November 2013

# FQNL2N50B **N-Channel QFET® MOSFET**

500 V, 0.35 A, 5.3  $\Omega$ 

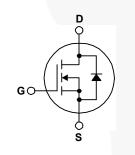
### Description

This N-Channel enhancement mode power MOSFET is • 0.35 A, 500 V,  $R_{DS(on)}$  = 5.3  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state  $\cdot$  Low Gate Charge (Typ. 6 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 4 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- I<sub>D</sub> = 0.175 A





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

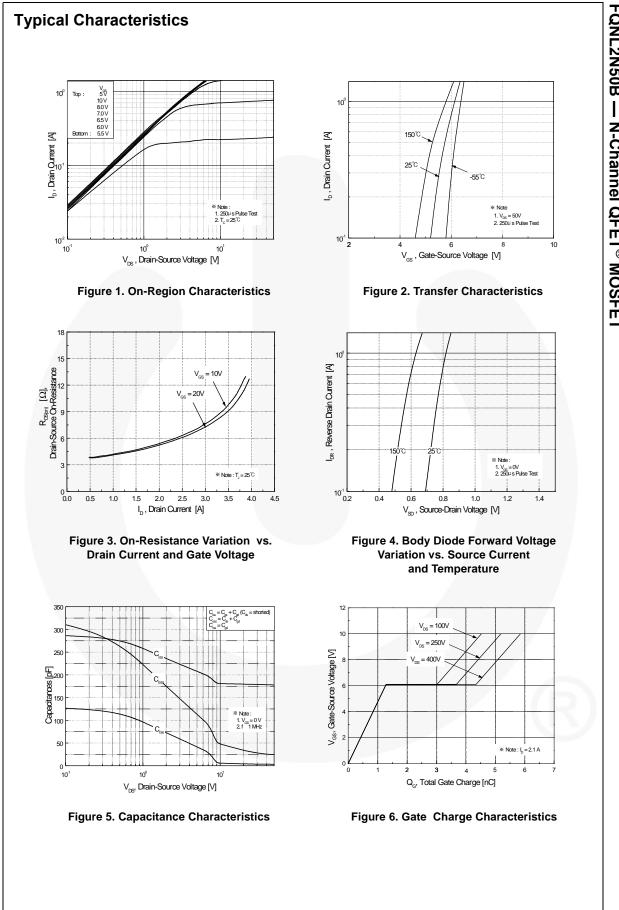
Symbol	Parameter		FQNL2N50BTA	Unit
V <sub>DSS</sub>	Drain-Source Voltage		500	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		0.35	А
	- Continuous (T <sub>C</sub> = 100°C)		0.22	A
DM	Drain Current - Pulsed (I	lote 1)	1.4	A
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
AR	Avalanche Current (I	lote 1)	0.35	A
E <sub>AR</sub>	Repetitive Avalanche Energy (I	lote 1)	0.15	mJ
dv/dt	Peak Diode Recovery dv/dt (I	lote 2)	4.5	V/ns
D	Power Dissipation ( $T_C = 25^{\circ}C$ )		1.5	W
	- Derate above 25°C		0.012	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum lead temperature for soldering,		300	°C
-	1/8" from case for 5 seconds.			

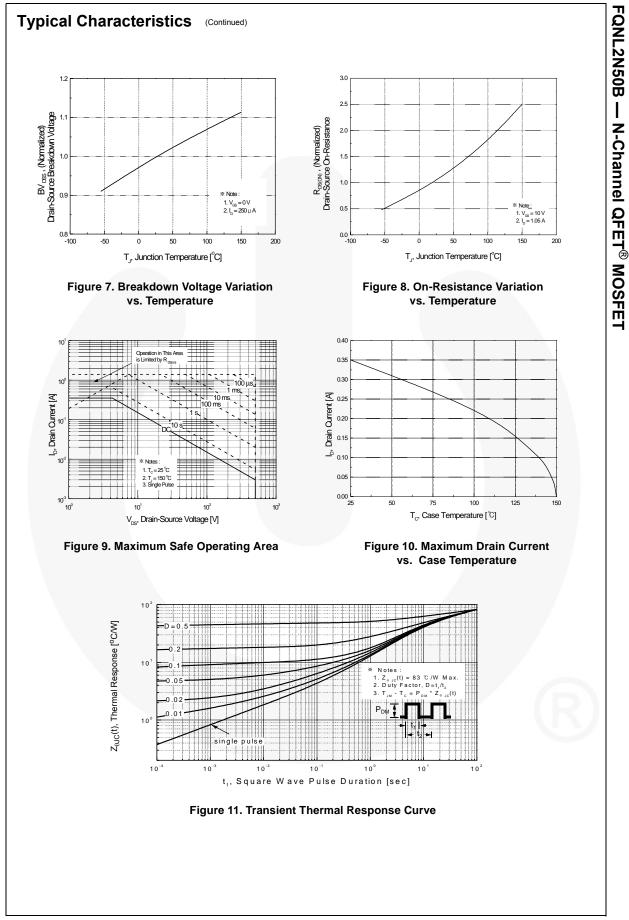
### **Thermal Characteristics**

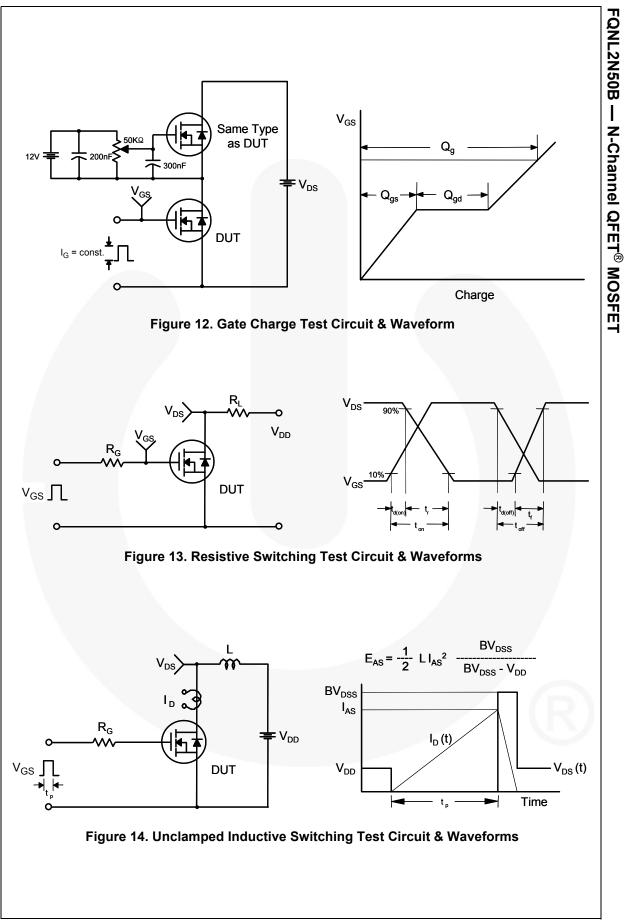
Symbol	Parameter	FQNL2N50BTA	Unit	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	83	°C/W	

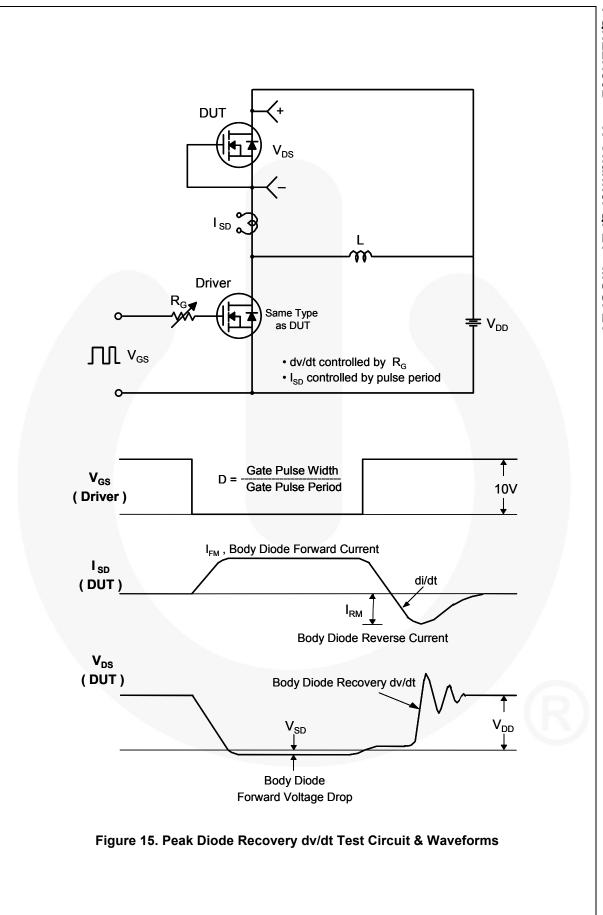
Part Number To		Top Mark Pack		kage Packing Method Reel		Size	Tape Width		Quantity		
FQNL2N50BTA FQNL2N50B		TO-92L		AM	МО	N/	A	N/A		2000 units	
lectri	cal Cha	racteristics	T <sub>C</sub> = 25°C	unless oth	erwise noted.						
Symbol		Parameter			Test Con	ditions		Min.	Тур.	Max	. Unit
Off Cha	aracterist	ics									
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage			$V_{GS}$ = 0 V, $I_{D}$ = 250 $\mu$ A			500			V	
ΔΒV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient			$I_D = 250 \ \mu$ A, Referenced to 25°C				0.48		V/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current		V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V					1	μA		
			ent	V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C					10	μA	
I <sub>GSSF</sub>	Gate-Body	y Leakage Current, F	orward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V					100	nA	
I <sub>GSSR</sub>	Gate-Body	y Leakage Current, F	Reverse	$V_{GS}$ = -30 V, $V_{DS}$ = 0 V					-100	nA	
On Cha	racterist	ics									
V <sub>GS(th)</sub>	1	Gate Threshold Voltage		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA			2.3	3.0	3.7	V	
00(11)				$V_{DS} = V_{GS}, I_{D} = 250 \text{ mA}$				3.6	4.3	5.0	V
R <sub>DS(on)</sub>	Static Dra On-Resist			V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.175 A				4.2	5.3	Ω	
9 <sub>FS</sub>	Forward T	ransconductance		V <sub>DS</sub> =	50 V, I <sub>D</sub> = 0	175 A			0.72		S
Dynam	ic Charac	teristics									
C <sub>iss</sub>	Input Capa	acitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,			180	230	pF		
C <sub>oss</sub>	Output Ca	pacitance		f = 1.0					30	40	pF
C <sub>rss</sub>	Reverse T	ransfer Capacitance	•						4	6	pF
Switchi	ing Chara	acteristics									
t <sub>d(on)</sub>	Turn-On D	elay Time		Vaa =	250 V, I <sub>D</sub> =	214			6	20	ns
t <sub>r</sub>	Turn-On F	Rise Time		$R_G = 2$	_	2.17,			25	60	ns
t <sub>d(off)</sub>	Turn-Off D	elay Time							10	30	ns
t <sub>f</sub>	Turn-Off F	all Time				(	Note 3)		20	50	ns
Qg	Total Gate	Charge		$V_{DS} = -$	400 V, I <sub>D</sub> =	2.1 A,			6.0	8.0	nC
Q <sub>gs</sub>	Gate-Sour	rce Charge		V <sub>GS</sub> =					1.3		nC
Q <sub>gd</sub>	Gate-Drai	n Charge		_		(	Note 3)		3.0		nC
	ource Di	ode Characteri	stics ar	nd Max	imum Ra	atinas					
I <sub>S</sub>				Diode Forward Current						0.35	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current						1.4	A			
V <sub>SD</sub>		rce Diode Forward \			0 V, I <sub>S</sub> = 0.3	5 A				1.4	V
t <sub>rr</sub>		Recovery Time	5		0 V, I <sub>S</sub> = 2.1				195		ns
Q <sub>rr</sub>		Recovery Charge		$dl_{\rm F} / dt = 100 \text{ A}/\mu \text{s}$				0.69		μC	

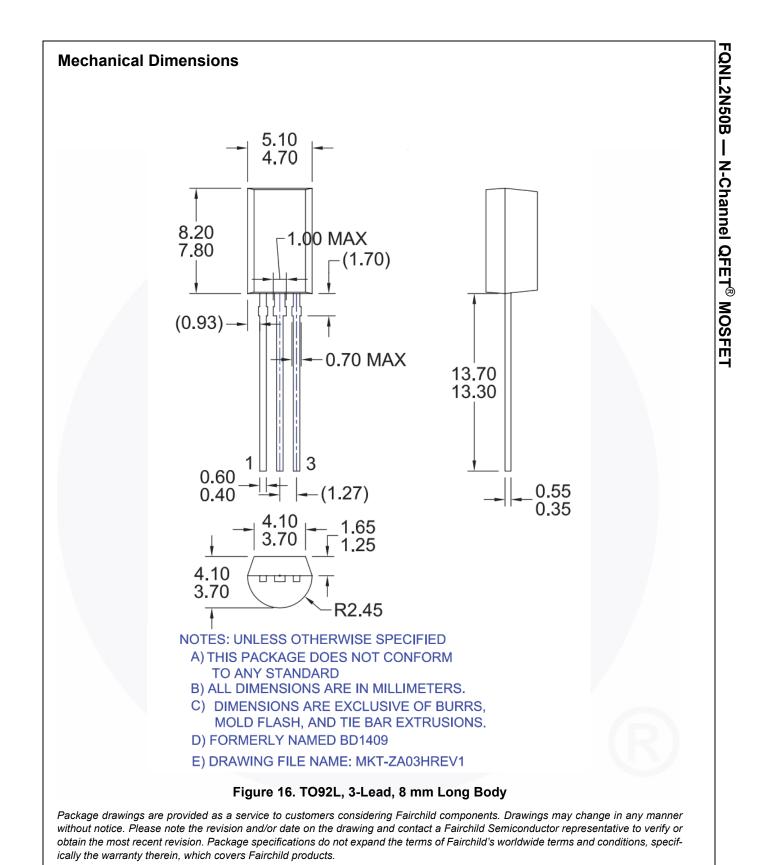
**Notes:** 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2.  $I_{SD} \leq 2.1 \text{ A}$ , di/dt  $\leq 200 \text{ A/}\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^{\circ}\text{C}$ . 3. Essentially independent of operating temperature.











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http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TO92-H03



Advance Information

Preliminary

No Identification Needed

Obsolete

Formative / In Design

First Production

**Full Production** 

Not In Production

notice to improve design.

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